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*Eric Ringer**eric.ringer@tkhr.com***FACSIMILE TRANSMISSION**

August 13, 2004

**[062002-1751]*****TO***

Parvis Hassanzadeh

***FROM***

Eric Ringer

**FAX: 571 273 1435****FAX: 770-951-0933****TEL: 571 272 1435****TEL: 770 933 9500****RE: 09/855,978**

(Message) Examiner Hassanzadeh, this is transmission 4 of 5.

**Number of Pages (Including This Cover Sheet): - 28 - Page(s)**  
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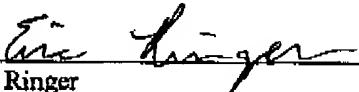
PAGE 1/28 \* RCVD AT 8/13/2004 12:22:37 PM [Eastern Daylight Time] \* SVR:USPTO-EFXRF-3/24 \* DNIS:2731435 \* CSID: \* DURATION (mm:ss):11-38

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I hereby certify that this correspondence is being transmitted by facsimile to:

**ATTN: Parvis Hassanzadeh**  
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Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

on August 13, 2004.

  
Eric Ringer

In re application of: **Kevin P. Martin et al.** Confirmation No.: **1603**  
U.S. Serial Number: **09/855,972** Art Unit: **1763**  
Filing Date: **May 15, 2001** Examiner: **Hassanzadeh, Parvis**  
Our Reference Number: **62002-1751**

Title: **Method and Apparatus for Low Energy Electron Enhanced Etching or  
Substrates in an AC or DC Plasma Environment**

**3 Cited References (Articles Only)**